CSD18532KCS 60-V N-Channel NexFET™ Power MOSFET

1 Features

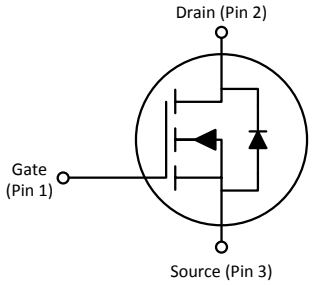
- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- TO-220 Plastic Package

2 Applications

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Motor Control

3 Description

This 60 V, 3.3 mΩ, TO-220 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.





Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	60		V
Q_g	Gate Charge Total (10 V)	44		nC
Q_{gd}	Gate Charge Gate-to-Drain	6.9		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 4.5 V	4.2	mΩ
		V_{GS} = 10 V	3.3	mΩ
$V_{GS(th)}$	Threshold Voltage	1.8		V

Ordering Information(1)

Device	Package	Media	Qty	Ship
CSD18532KCS	TO-220 Plastic Package	Tube	50	Tube

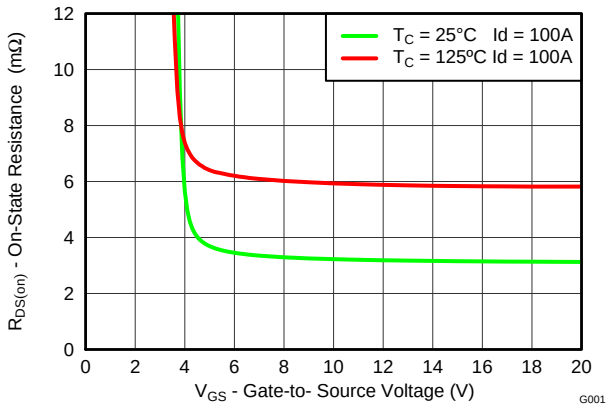
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

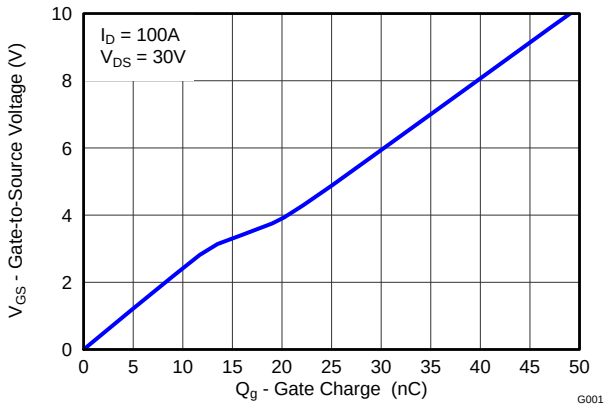
T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited), T_C = 25°C	100	A
	Continuous Drain Current (Silicon limited), T_C = 25°C	169	
	Continuous Drain Current (Silicon limited), T_C = 100°C	116	
I_{DM}	Pulsed Drain Current (1)	400	A
P_D	Power Dissipation	250	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 175	°C
E_{AS}	Avalanche Energy, single pulse I_D = 75 A, L = 0.1 mH, R_G = 25 Ω	281	mJ

(1) Pulse duration ≤300 µs, duty cycle ≤2%

$R_{DS(on)}$ vs V_{GS}



Gate Charge



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (October 2012) to Revision B **Page**

- Increased I_D at T_C = 100°C to 116 A ... 1
- Increased I_{DM} to 400 A ... 1
- Increased max operating junction and storage temperature to 175°C ... 1
- Updated Figure 1 from a normalized $R_{\theta JA}$ to an $R_{\theta JC}$ curve ... 4
- Updated Figure 6 to extend to 175°C ... 5
- Updated Figure 8 to extend to 175°C ... 5
- Updated the SOA in Figure 10 ... 6
- Updated Figure 12 to extend to 175°C ... 6

Changes from Original (August 2012) to Revision A **Page**

- Changed the Transconductance TYP value From: 146 S To: 187 S ... 3
- Changed $R_{\theta JA}$ From: MAX = 62°C/W To: MAX = 65°C/W ... 3
- Changed Figure 2 ... 4

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5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 250 µA	60			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0 V, V_{DS} = 48 V			1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	1.5	1.8	2.2	V
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 4.5 V, I_D = 100 A		4.2	5.3	mΩ
		V_{GS} = 10 V, I_D = 100 A		3.3	4.2	mΩ
g_{fs}	Transconductance	V_{DS} = 30 V, I_D = 100 A		187		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 30 V, f = 1 MHz		3900	4680	pF
C_{oss}	Output Capacitance			470	564	pF
C_{rss}	Reverse Transfer Capacitance			11	14	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (4.5 V)	V_{DS} = 30 V, I_D = 100 A		21	25	nC
Q_g	Gate Charge Total (10 V)			44	53	nC
Q_{gd}	Gate Charge Gate-to-Drain			6.9		nC
Q_{gs}	Gate Charge Gate-to-Source			10		nC
$Q_{g(th)}$	Gate Charge at V_{th}			7.3		nC
Q_{oss}	Output Charge	V_{DS} = 30 V, V_{GS} = 0 V		52		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 30 V, V_{GS} = 10 V, I_{DS} = 100 A, R_G = 0 Ω		7.8		ns
t_r	Rise Time			5.3		ns
$t_{d(off)}$	Turn Off Delay Time			24.2		ns
t_f	Fall Time			5.6		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 100 A, V_{GS} = 0 V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 30 V, I_F = 100 A, di/dt = 300 A/µs		127		nC
t_{rr}	Reverse Recovery Time			57		ns

5.2 Thermal Information

(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.6	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	

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5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

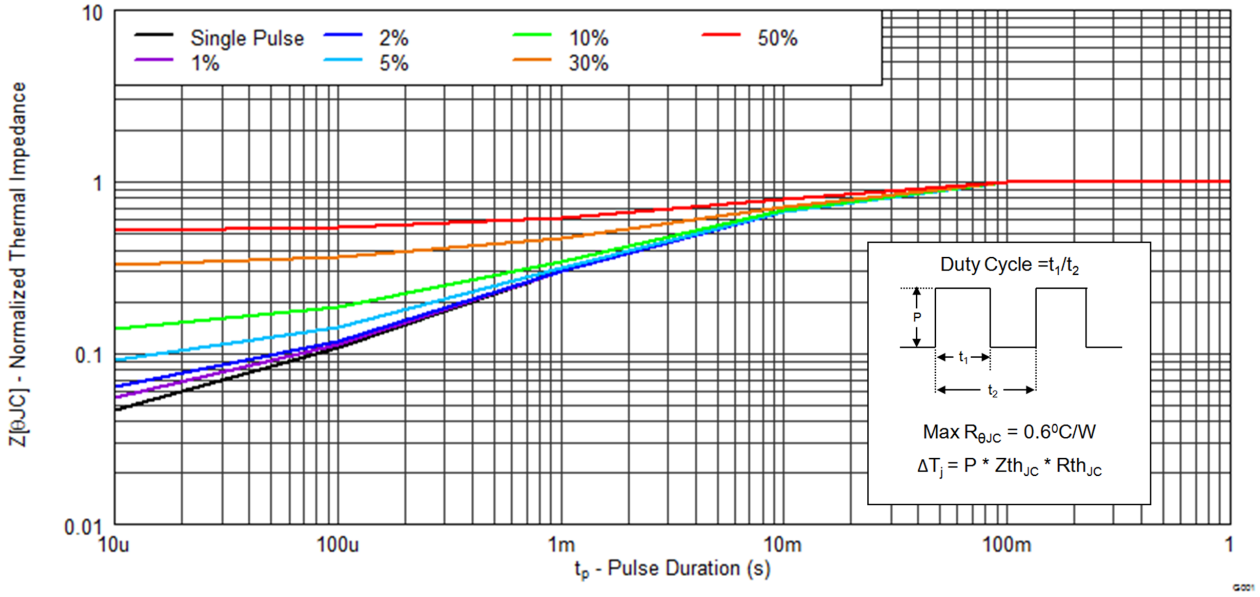


Figure 1. Transient Thermal Impedance

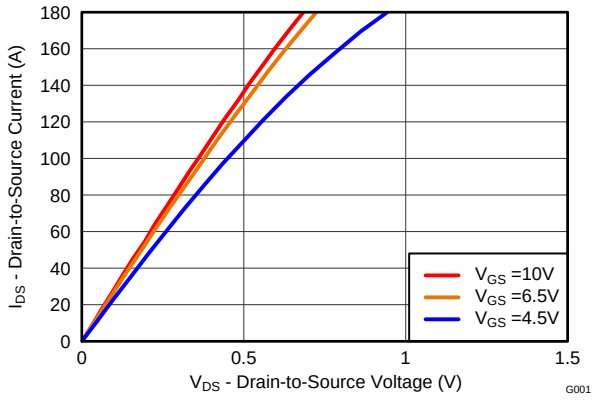


Figure 2. Saturation Characteristics

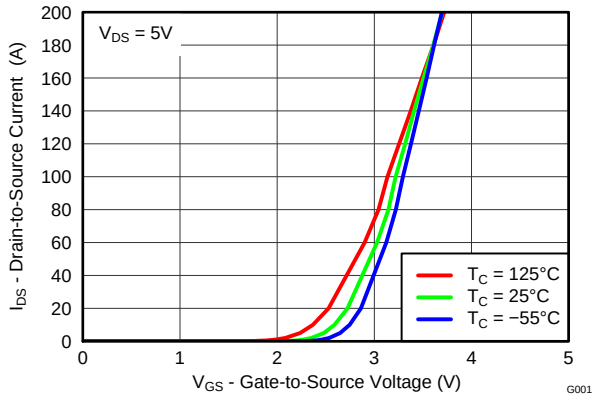


Figure 3. Transfer Characteristics

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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

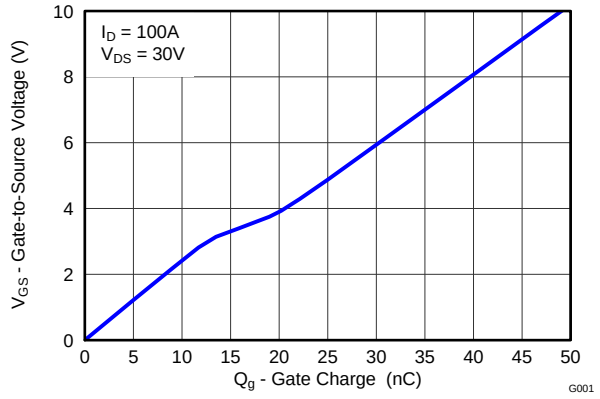


Figure 4. Gate Charge

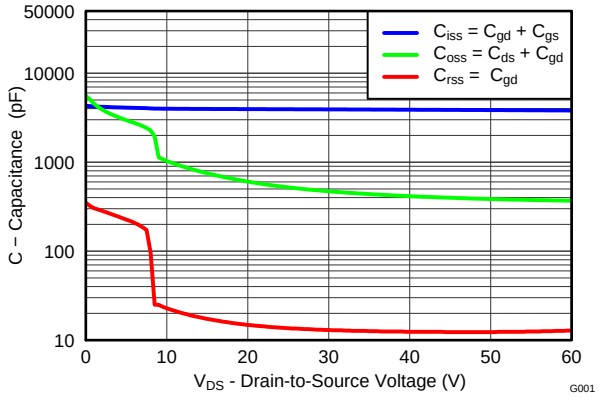


Figure 5. Capacitance

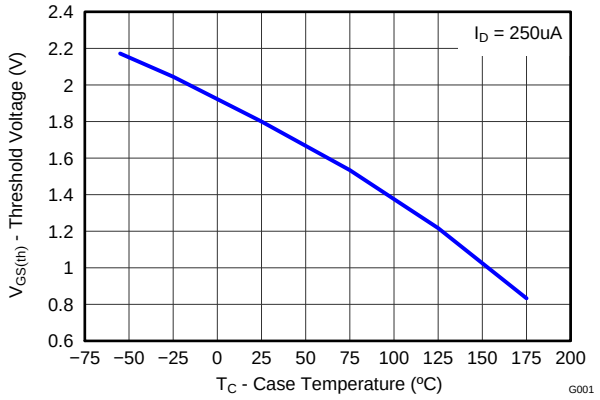


Figure 6. Threshold Voltage vs Temperature

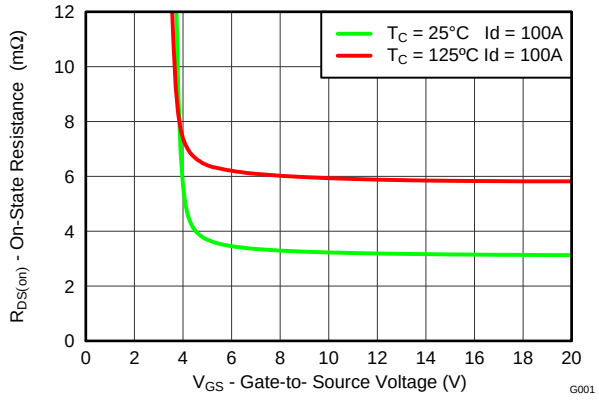


Figure 7. On-State Resistance vs Gate-to-Source Voltage

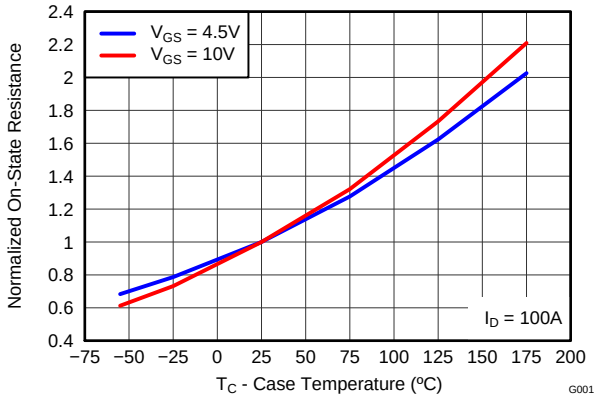


Figure 8. Normalized On-State Resistance vs Temperature

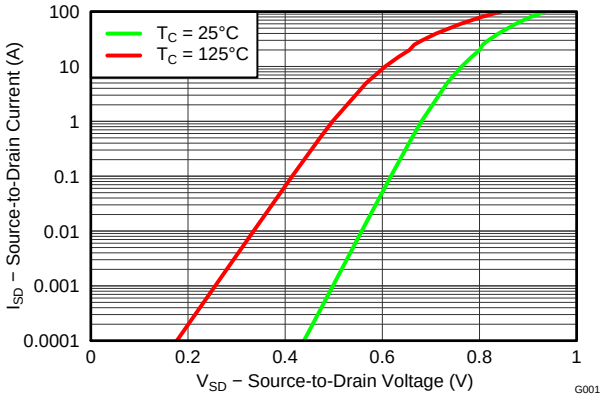


Figure 9. Typical Diode Forward Voltage

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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

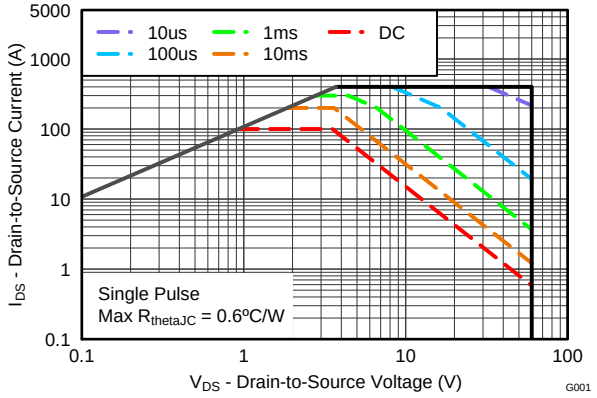


Figure 10. Maximum Safe Operating Area

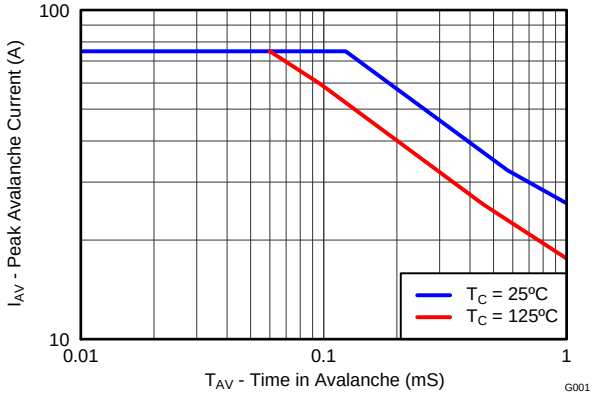


Figure 11. Single Pulse Unclamped Inductive Switching

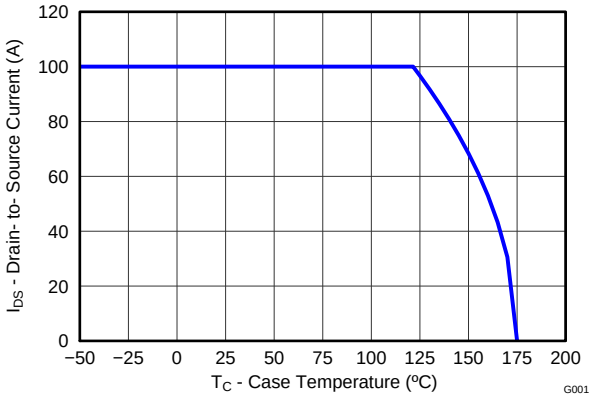


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — *TI Glossary*.

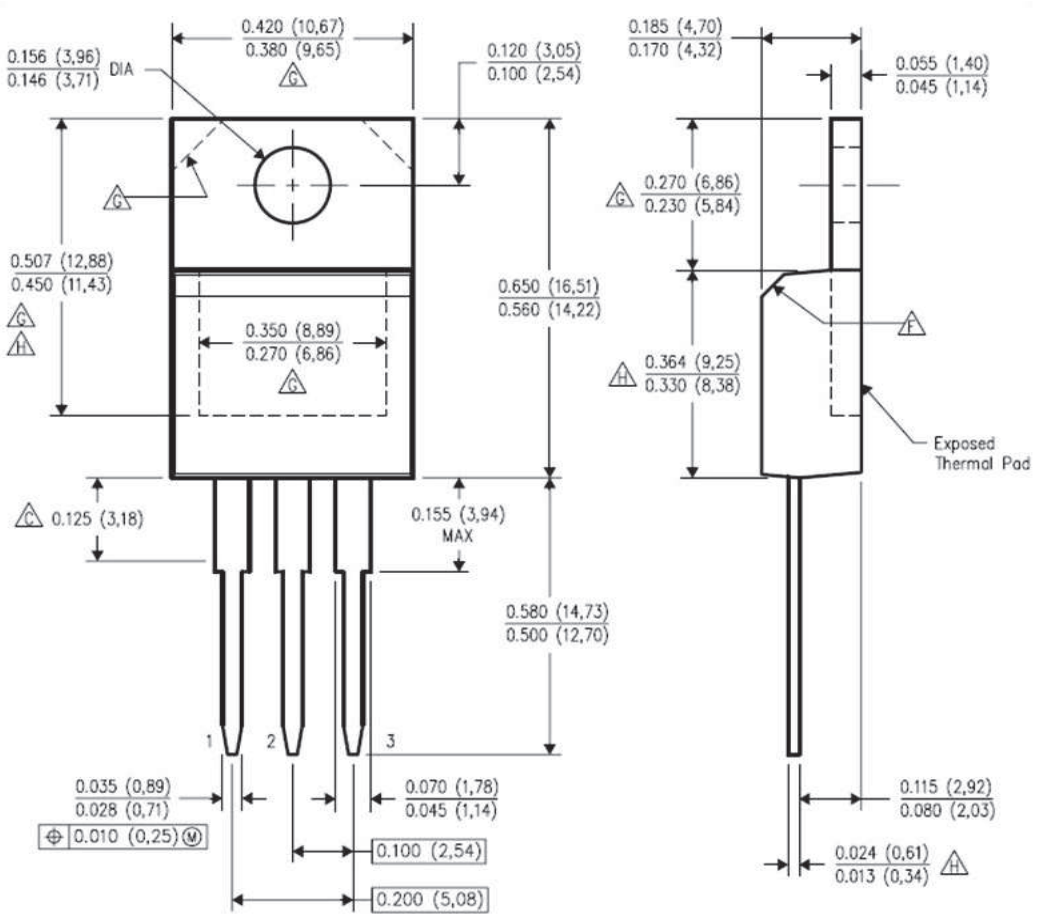
This glossary lists and explains terms, acronyms, and definitions.

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7 Mechanical Data

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 KCS Package Dimensions



Notes:

1. All linear dimensions are in inches.
2. This drawing is subject to change without notice.
3. Lead dimensions are not controlled within 'C' area.
4. All lead dimensions apply before solder dip.
5. The center lead is in electrical contact with the mounting tab.
6. The chamfer at 'F' is optional
7. Thermal pad contour at 'G' optional with these dimensions
8. 'H' Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.

Pin Configuration

Position	Designation
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD18532KCS	ACTIVE	TO-220	KCS	3	50	Green (RoHS & no Sb/Br)	SN	N / A for Pkg Type	-55 to 175	CSD18532KCS	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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